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LSST Camera Sensor Characterisation and pre-commissioning (LSST:UK WP 3.9)

Dan Weatherill, Ian Shipsey, Farrukh Azfar, Jeff Tseng



Oxford Physics Microstructure Detector
Laboratory

Outline



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- LSST camera & sensors specs recap
- Brief history of LSST:UK WP3.9 “phase A” & “phase B” contributions
 - Clock timing & optimisation
 - Measurement of Si di-vacancy
 - Effect of gate width on brighter-fatter effect
 - (ongoing) oversampled PSF measurement
 - ~~(ongoing) TCAD modelling~~ **(NO TIME!)**
- Commissioning progress & upcoming commissioning assistance (LSST:UK “in-kind” contribution)
- Other (none LSST:UK funded) Oxford “in-kind” efforts

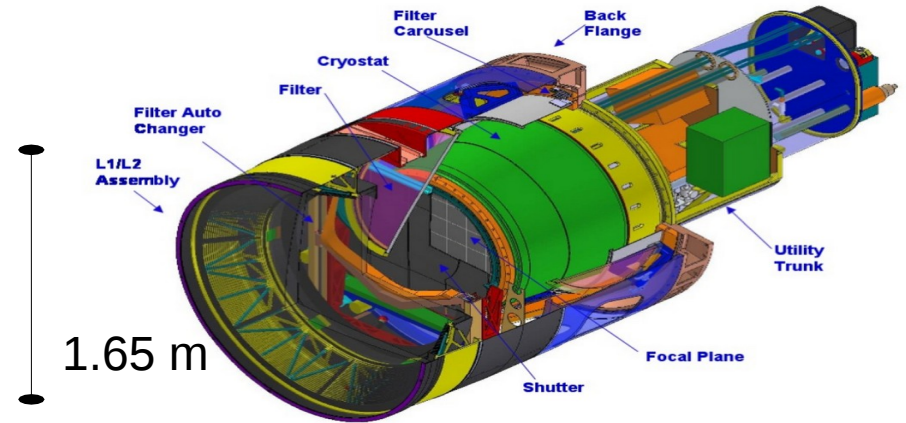


Image: LSST Science Book

The LSST Camera



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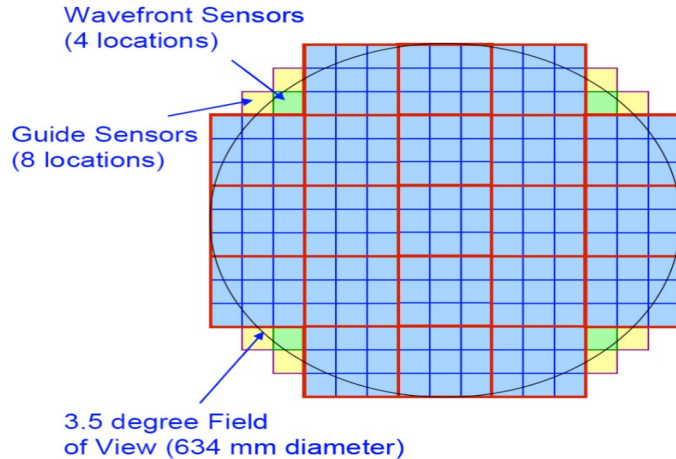


Image: LSST Science Book

- **Fast Optics needed for “fast” and “deep” survey.**
- **Small pixels – to make sure we can oversample the PSF of the optics**

- Operating temperature: -100 Celsius
- Challenging mechanical requirements: fast (mechanical!!) shutter & filter changer
- Fast (f/1.2) optics lead to stringent flatness specification ($\leq 20\mu\text{m}$ over whole focal plane!).
- Focal plane consists of 189 4k x 4k science sensors arranged in “rafts” of 9 (3.2 Gpix total). **Comcam is one such “raft”.**
- 10 μm pixel pitch
- 6 Filters cover wavelength range from 300nm – 1100nm
- High visit rate demands fast readout ($\sim 2\text{s}$).
- To maintain reasonable noise ($\sim 4e^-$), CCD must be **highly segmented (16 outputs)**. This implies a **pixel rate of $\sim 550\text{kHz}$.**
- $9 * 21 * 16 = 3024$ channels of video!

Achieving High QE

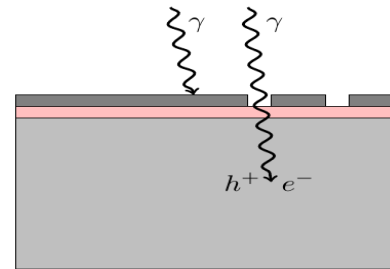
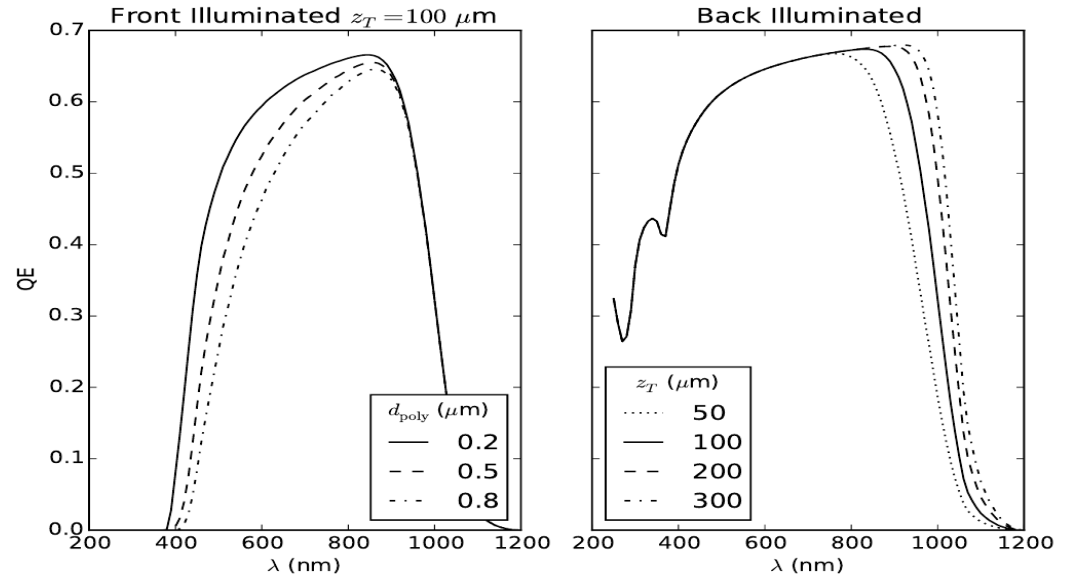


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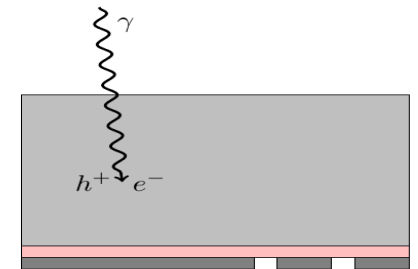
- LSST filter bands (below left) cover near UV to near IR. To maintain survey depth in brief exposure times, high **Quantum Efficiency** is key.
- Blue end QE is enhanced by back illumination (removing poly and gate absorption) and adding AR coating
- Maintaining high QE at long wavelengths implies a thick detector.
- LSST science detector is 100 μm thick.
- Absorption length is also (slightly) temperature dependent.
- High resistivity bulk material ($>10\text{k } \Omega \text{ cm}$!!!) is used for construction

$$QE_{FI} = (1 - R(\lambda)) e^{-\alpha(\lambda)d_{\text{poly}}} \left(1 - e^{-\alpha(\lambda)z_T}\right)$$

$$QE_{BI} = (1 - R(\lambda)) \left(1 - e^{-\alpha(\lambda)z_T}\right)$$



Front Illuminated

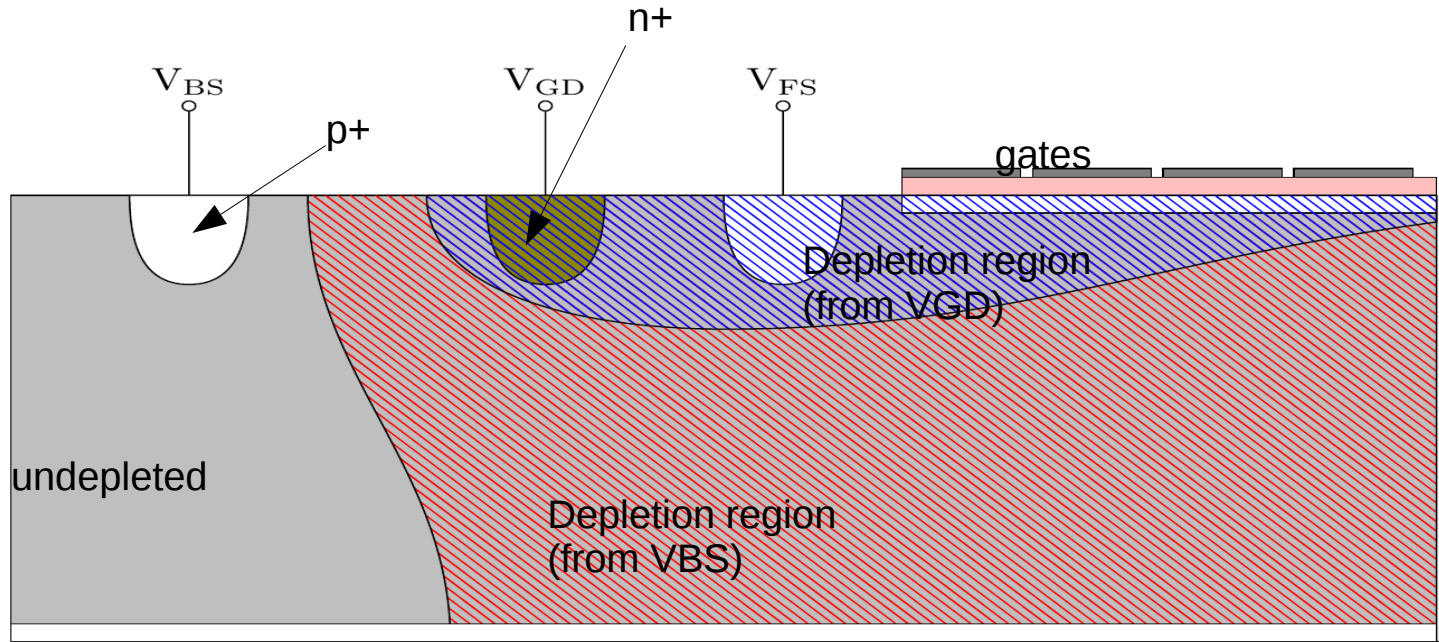


Back Illuminated

Deep Depletion CCDs



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A thick detector implies a long drift time for electron collection. This, in turn, implies a large diffusion radius

$$r_{\text{diff}} = z_T \sqrt{\frac{2k_B T}{q_e V_{\text{coll}}}}$$

- To reduce the collection time of charges (and thus the diffusion radius), a high bias voltage is applied to the back side of the chip. Unfortunately, unchecked, this turns the chip into an expensive resistive heater
- In order to prevent leakage currents from the front substrate to the back, guard drains are included in the design which creates a protective depletion region whilst the back bias is applied

CCD Summary



Confinement is by gates down columns, and channel stop implants along rows (as with any CCD pixel!).

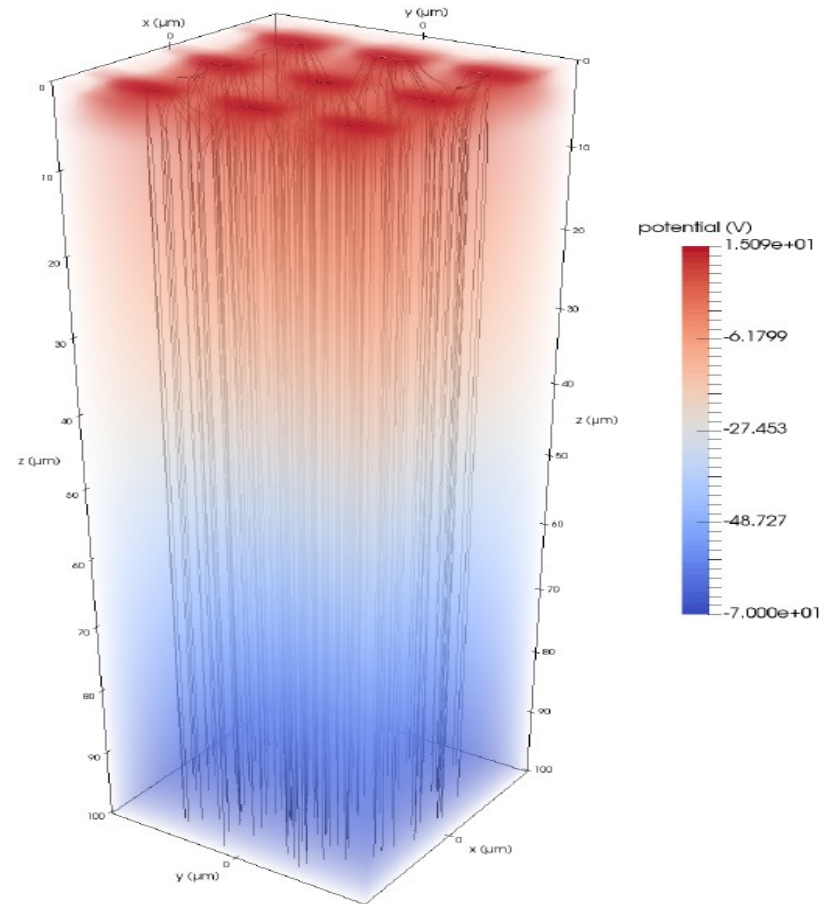
Recall LSST pixels are small in area, but very deep (right: electrostatic simulation of electron capture in CCD250 pixels).

The thickness of the CCD is what leads directly to effects such as: fringing, brighter-fatter effect.

It **indirectly** (via need for back biasing) leads to: complicated clocking and noise injection issues, “tearing”, “edge roll off”, “midline roll-off”, “astrometric scupper shift” etc etc.

High speed readout leads to complicated issues with clocking and timing for optimisation.

Should be emphasized: none of the technology needed for LSSTcam sensors was new/untried. What was new was putting it *all* into one chip!



A Tale of Two Teledyne CCDs



The devices in LSSTCam focal plane are a mixture of e2v CCD-250 and ITL/STA-3800C. Both are thick, back illuminated CCDs on high resistivity silicon.

But within that constraint, they almost couldn't be more different!

Adapting to the slight differences both mechanical and electro-optical has been challenging

Originally 2 separate manufacturers, e2v (Chelmsford, UK) and Teledyne / ITL / STA.

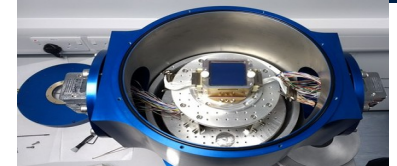
Teledyne acquired e2v in 2017, so technically these are now both Teledyne detectors

	CCD-250	STA-3800C
Imaging phases	4 (symmetric)	3 (asymmetric)
Output amp	2 stage MOSFET	1 stage JFET
construction	Back thinned, Si substrate	Glued glass substrate with lithoblack coating
Measured performance	Good noise, CTI, linearity	High FWC, better dark current

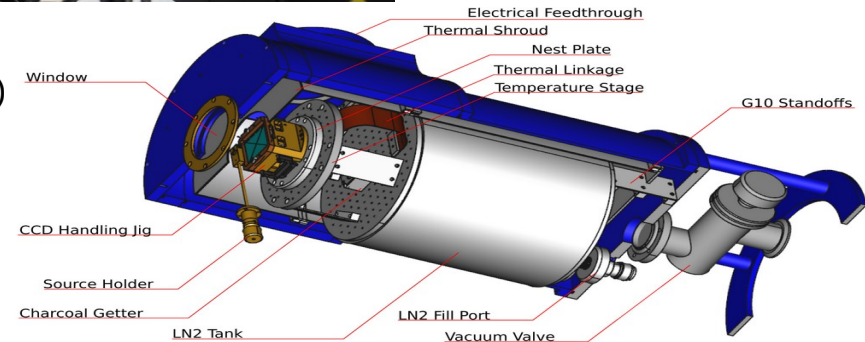
Oxford LSST Test System



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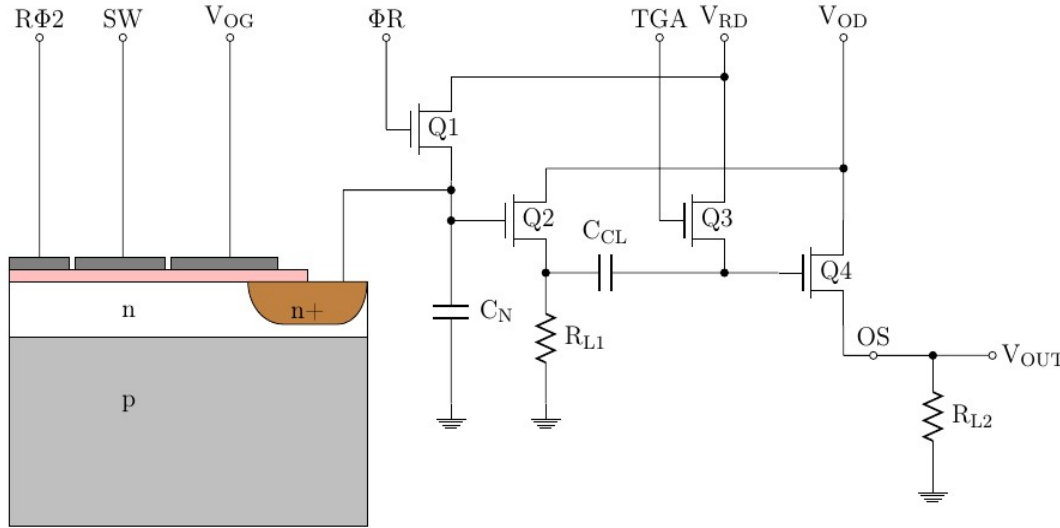
- LN2 cooling and active table for low vibration
- 250W QTH light source + monochromator (300nm – 1600nm wavelength)
- Online radiometry and spectroscopy (at integrating sphere)
- Can quickly integrating sphere with projection optics for PSF etc measurements.
- Operates at high vacuum ($1E-6$ mbar)
- Slightly different (but complementary) readout electronics than LSSTCam (by design!)



Readout Timing & Optimisation



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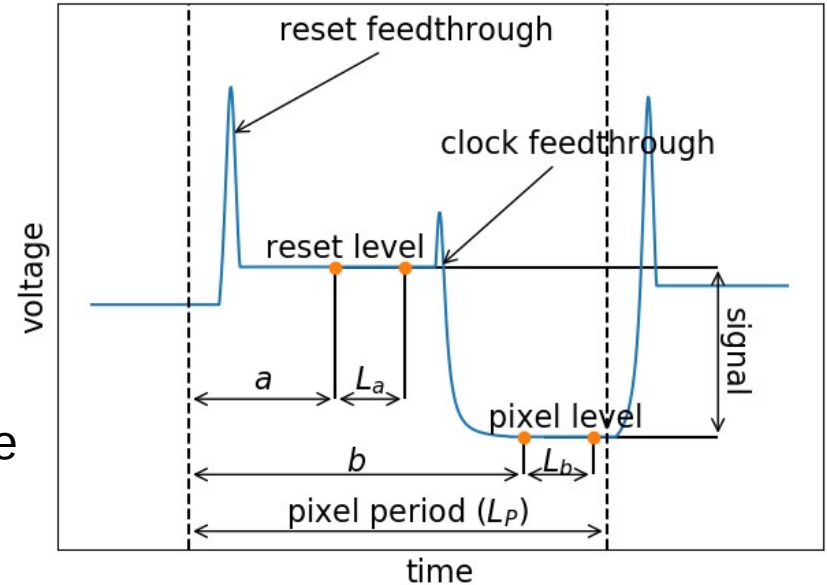


$$N_{\text{rms}} = \sqrt{\frac{k_B T}{C_N}}$$

Correlated Double Sampling (CDS) is one of a CCD's "secret weapons".

If you don't read out and subtract the reset ("kTC") noise at each pixel, it would **completely dominate** the noise spectrum.

LSSTCam uses custom designed analog front end ("ASPIC") chips to do this (digital too power costly!)



Readout Timing & Optimisation



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22 August 2019

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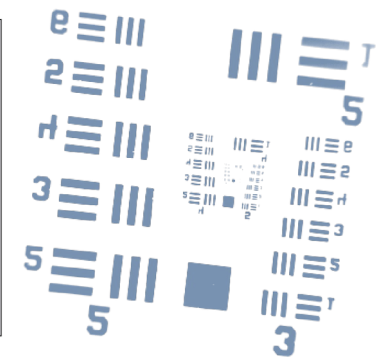
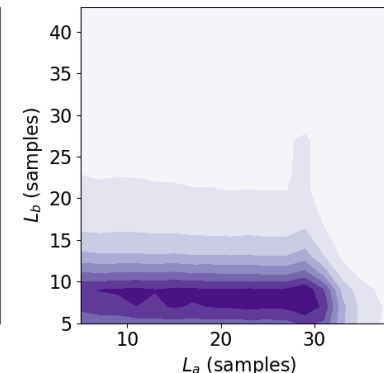
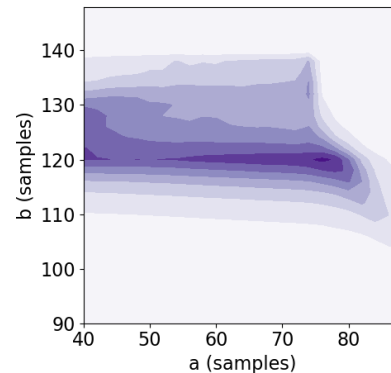
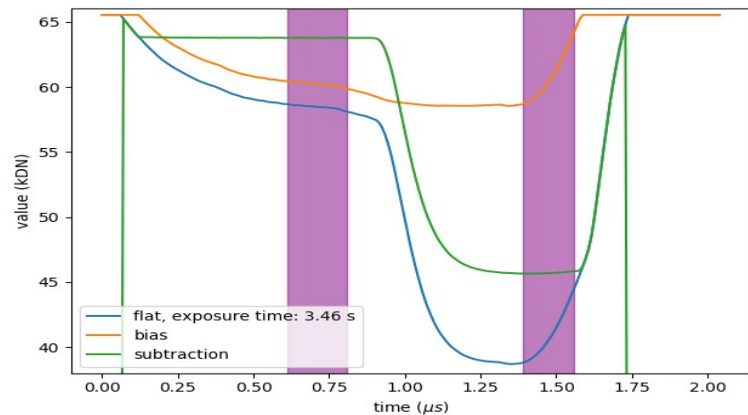
Automatic selection of correlated double sampling timing parameters

Daniel P. Weatherill, Ian Shipsey, Kirk Arndt, Richard Plackett, Daniel Wood, Kaloyan Metodiev, Maria Mironova, Daniela Bortoletto, Nicolas Demetriou

[Author Affiliations +](#)

J. of Astronomical Telescopes, Instruments, and Systems, 5(4), 041502 (2019) <https://doi.org/10.1117/1.JATIS.5.4.041502>

However, using digital CDS techniques we developed a new optimisation technique for the timing parameters of the CDS (in 2018/19). Can be used to minimise noise & maximise linearity of readout



Silicon di-vacancy measurement



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Charge transfer efficiency (CTE) of LSST sensors is very good, **however** we still have to worry about it because:

- We will be correcting for it anyway
- It interferes with correcting for brighter-fatter effect (ask if interested!)
- It turns out to be signal dependent in these devices, likely due to the “racetrack” device physics (again ask if interested)

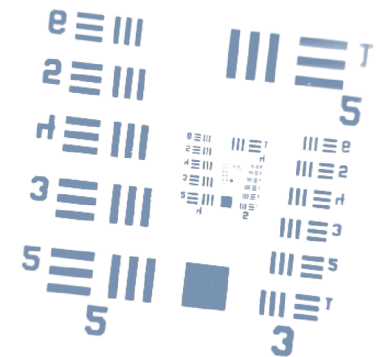
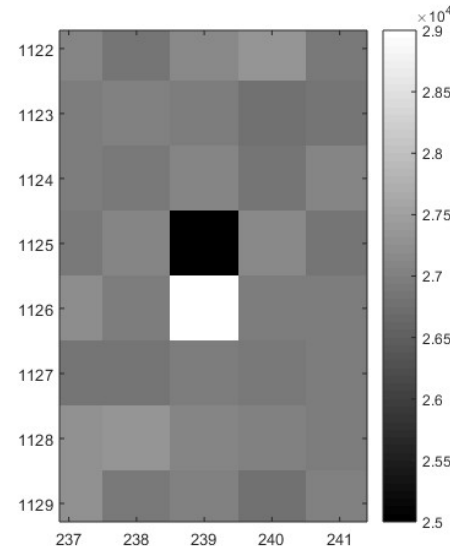
PROCEEDINGS OF SPIE

[SPIDigitalLibrary.org/conference-proceedings-of-spie](https://spiedigitallibrary.org/conference-proceedings-of-spie)

A study of the silicon divacancy defect in the E2V LSST CCD250 using the single trap pumping method

Wood, D., Weatherill, D., Shipsey, I. P. J., Plackett, R., Loreti, A., et al.

SPIE.

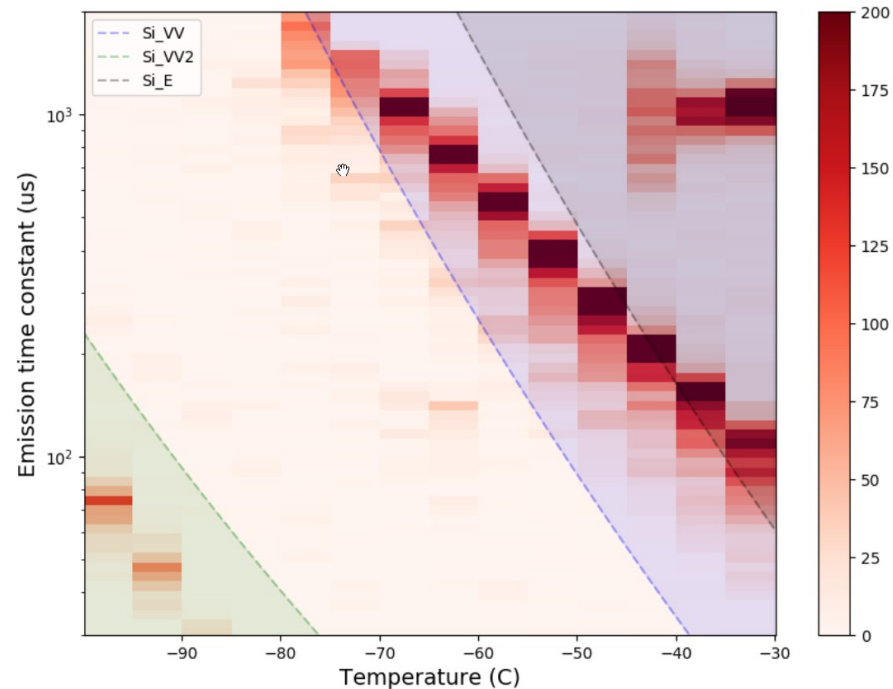


Divacancy trapping & CTI



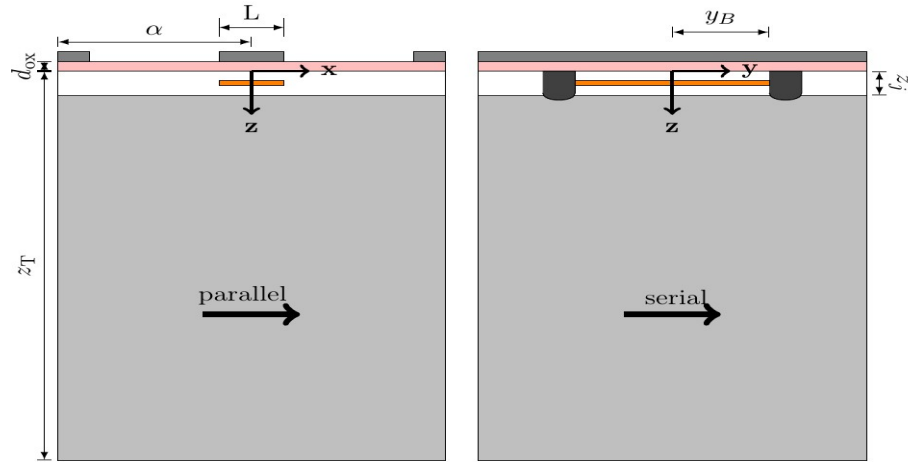
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- We used a technique called single trap pumping which can map out **individual** shallow level electron traps in the device, to survey the cause of the trapping component of the CTI (in 2019/ 2020)
- Confirmation that silicon di-vacancy traps are present at LSST camera operating conditions
- Verification that this is in addition to Roodman & Snyder's identification of "process" CTI traps in e2v CCD250 sensors
- Allows optimal readout timing conditions for minimising CTI to be determined (this has been tested!)
- **Side benefits**
 - Largest temperature range single-site trapping survey ever done on a CCD
 - First single-site trapping survey ever done on a high-rho bulk CCD
 - Interest also from other projects due to these facts (so far ESA Euclid & ESA PLATO)



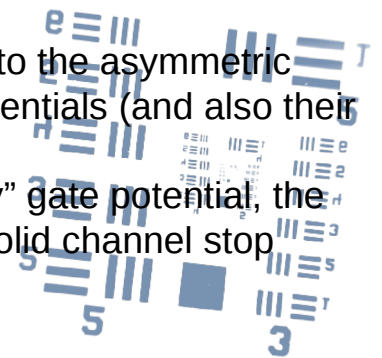
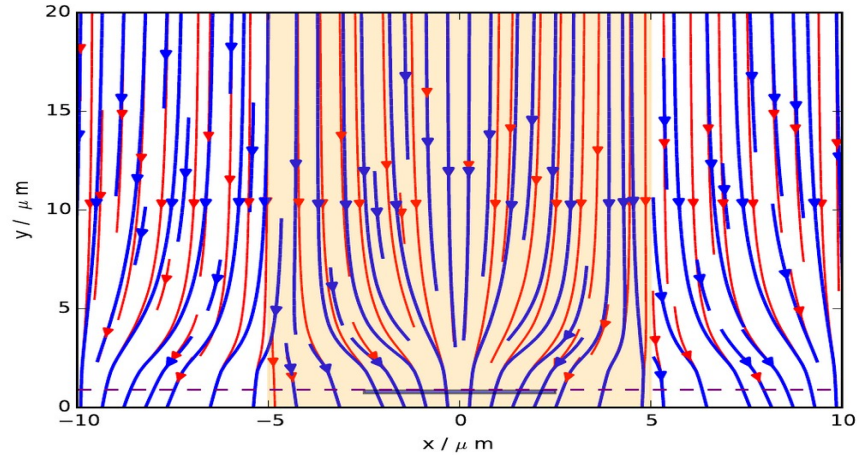
5 3

Brighter – Fatter Effect



- Gate
- Oxide
- n+ channel
- p+ bulk
- channel stop
- stored charge

- As charge accumulates in potential wells during integration, it causes the electric field structure of the pixel to change slightly, influencing the collection of further charge.
- This introduces correlations between nearby values in a flat field, and an increase in ellipticity of point sources (possibly serious for weak lensing measurement)
- One of the main areas of research into instrument signature removal, modelling and optical testing
- Effect is **asymmetric** due to the asymmetric nature of the collecting potentials (and also their “softness” in the device).
- One direction has “squishy” gate potential, the other direction has more solid channel stop potential

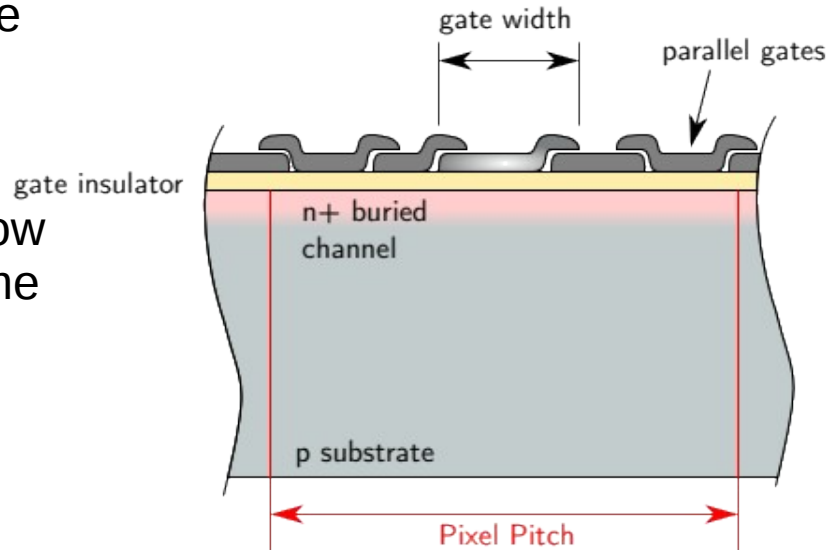


Gate Width Effect on Brighter-Fatter



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- Investigation into how the width of the CCD parallel gate affects the size of the brighter-fatter effect
- Gate widths determined at manufacture time, but can choose how many are energised at integration time



PROCEEDINGS OF SPIE

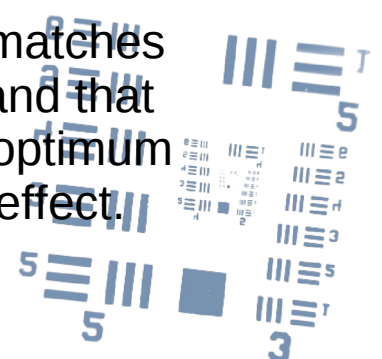
[SPIDigitalLibrary.org/conference-proceedings-of-spie](https://spiedigitallibrary.org/conference-proceedings-of-spie)

Measuring the impact of CCD gate width on the brighter-fatter effect

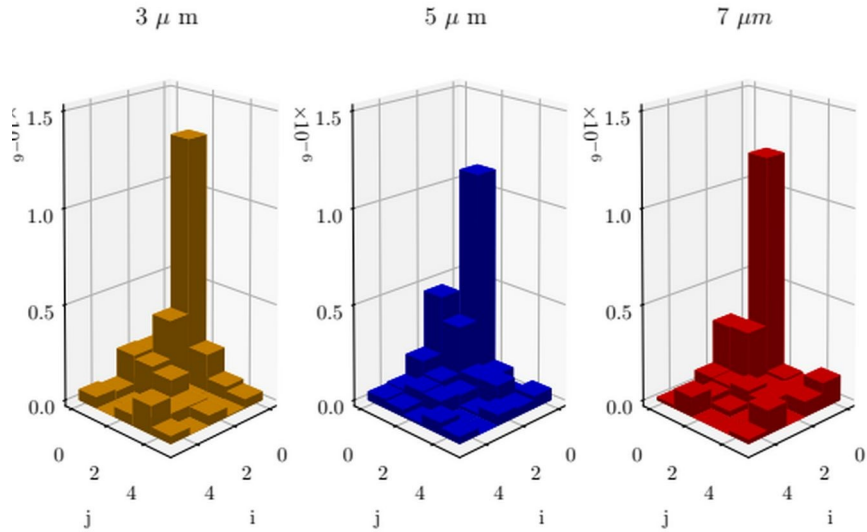
Weatherill, D., Wood, D., Shipsey, I. P. J., Plackett, R., Loreti, A., et al.

SPIE.

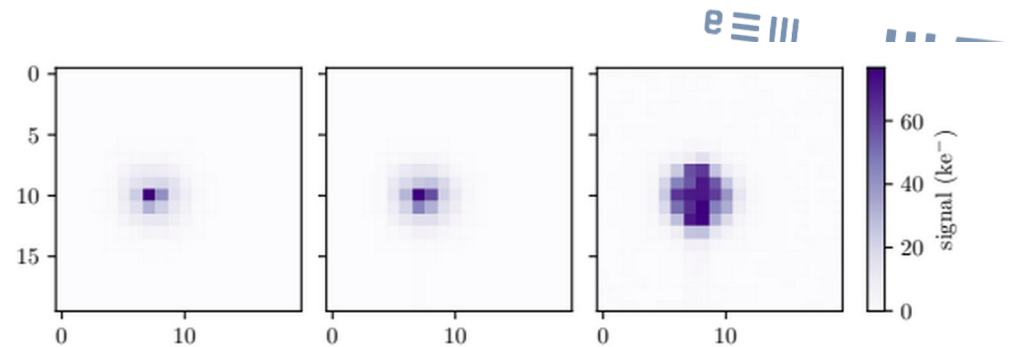
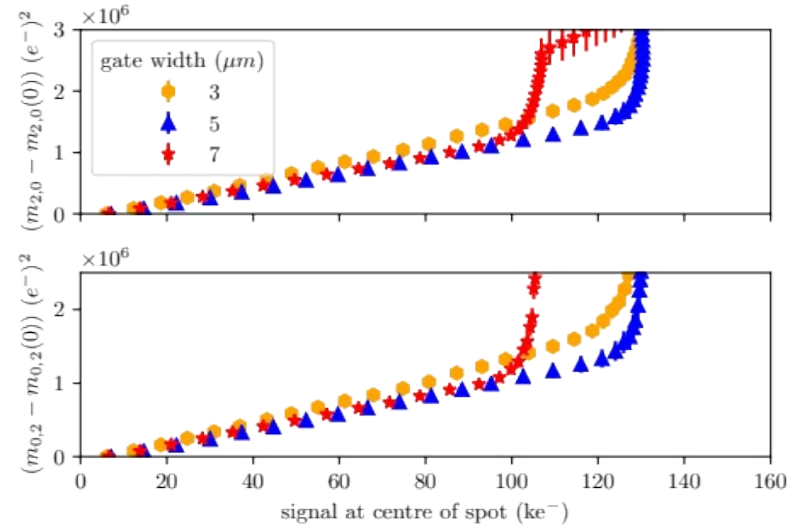
- Verified that this effect is there, that it matches the size expected due to simulations, and that the Isst camera is operating using the optimum gate widths to minimize brighter-fatter effect.



Gate width effect on brighter-fatter effect



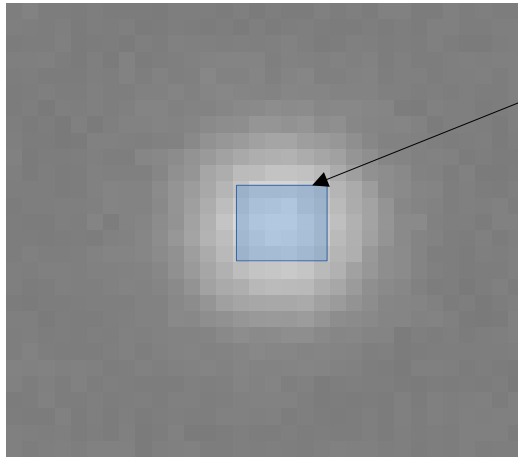
Accurate flat field correlation measurements (**above left**) correctly matched with direct spot projection measurements (**above right, right**)



Interferometric PSF Measurement



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LSST pixel
size

Idea we first had in 2016 , and first seriously contemplated in 2018:

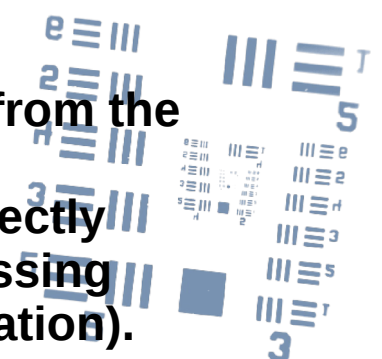
What if we could simultaneously project the same spot onto two detectors, such that we *know* that the optical field is close to identical?

Above: a way we checked the size of our optics spot projection early on!

Then we could:

1) easily de-convolve the optical spread from the device under test

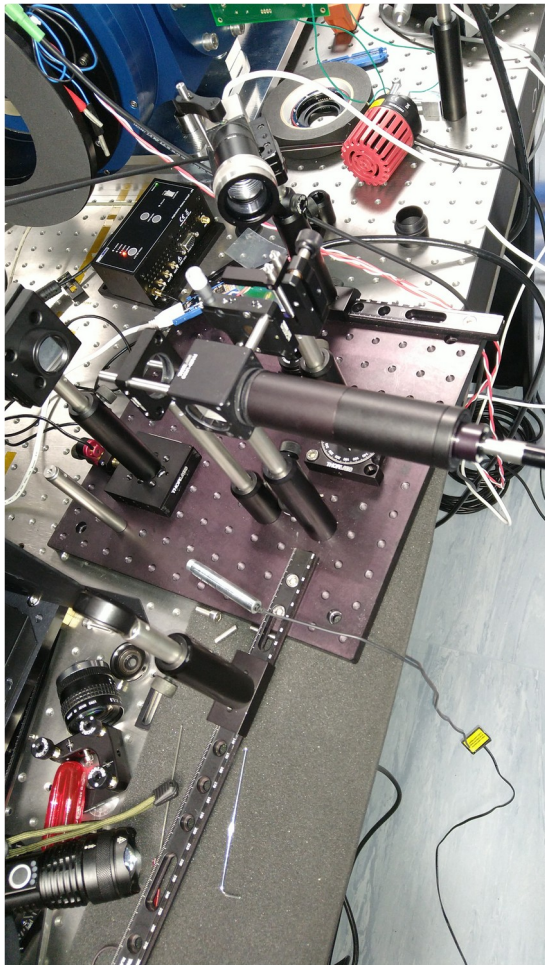
2) carefully do a lateral scan and do a directly oversampled measurement of its PSF! (bypassing Shannon-Whitaker-Nyquist limits on interpolation).



Interferometric Alignment

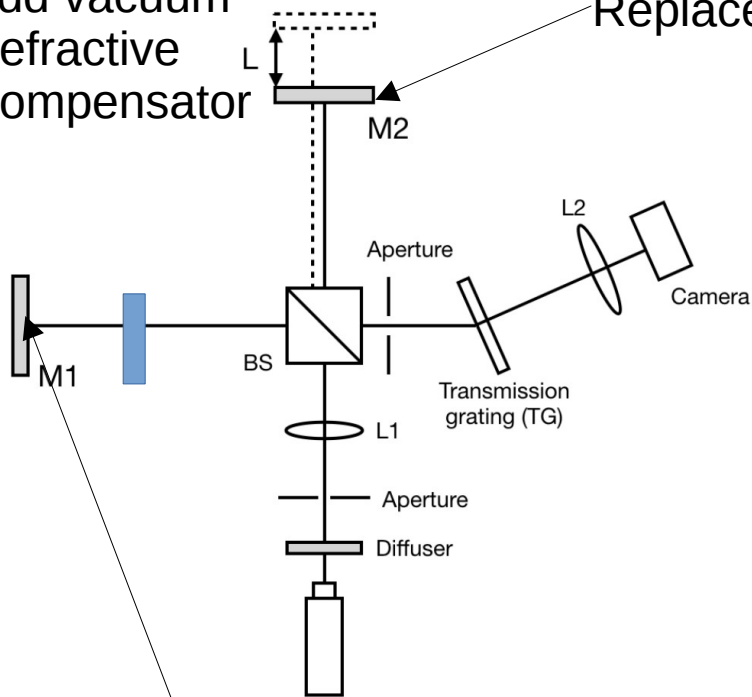


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Add vacuum
Refractive
Compensator

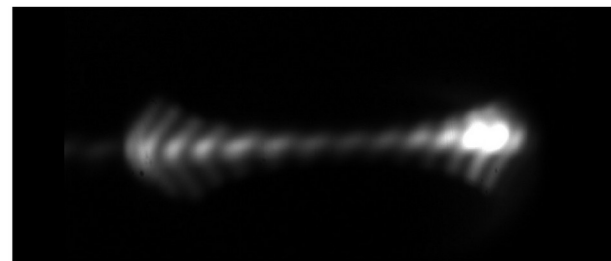
Replace with aux camera!



**Building a White
Light Spectrally
Channeled
Interferometer, to do
absolute optical path
difference
measurement
between two arms`**



Replace with CCD!



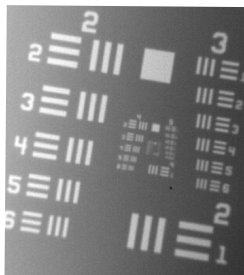
First Relative Projections



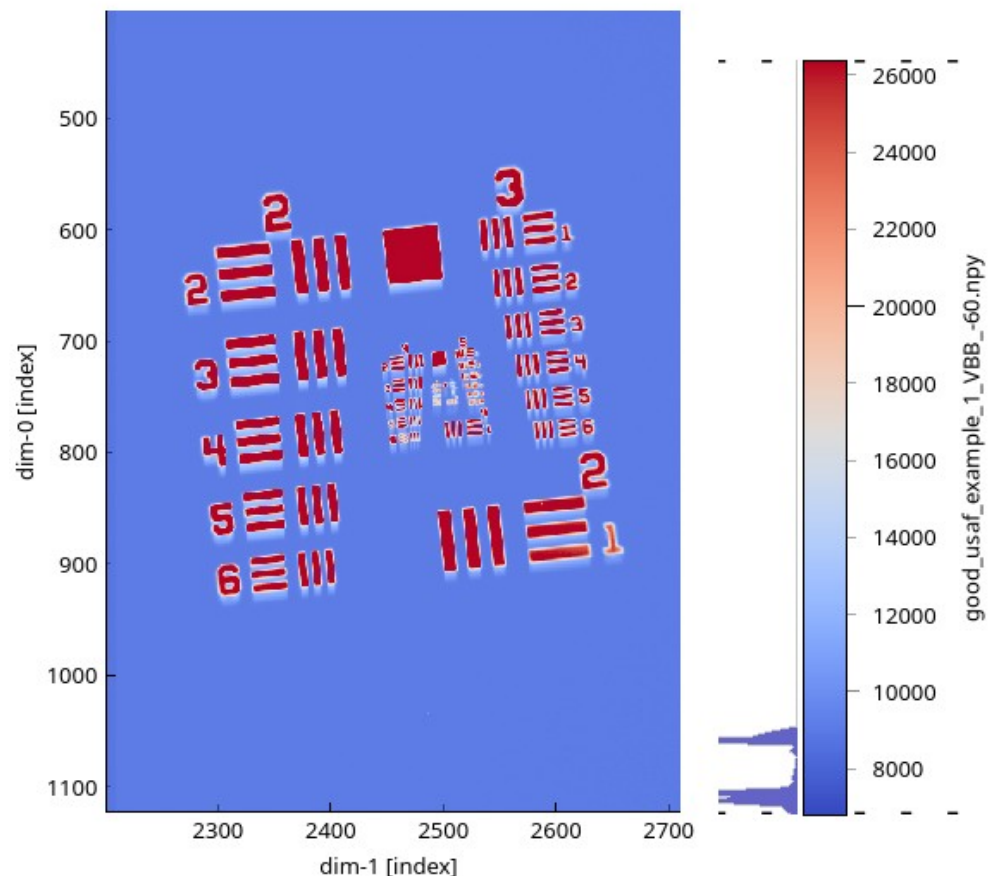
Early Results, don't take too seriously yet (work still in progress)!

Test images of a USAF test pattern projected through our interferometer imaged on LSST CCD (below), and aux test camera (right). Images shown at roughly relative pixel scale.

Note “trails” on test camera image, not 100% sure what the problem is yet, may be tilt though.



```
good_usaf_example_1_VBB_-60.npy -- good_usaf_example_1_VBB_-60.npy [:, :]
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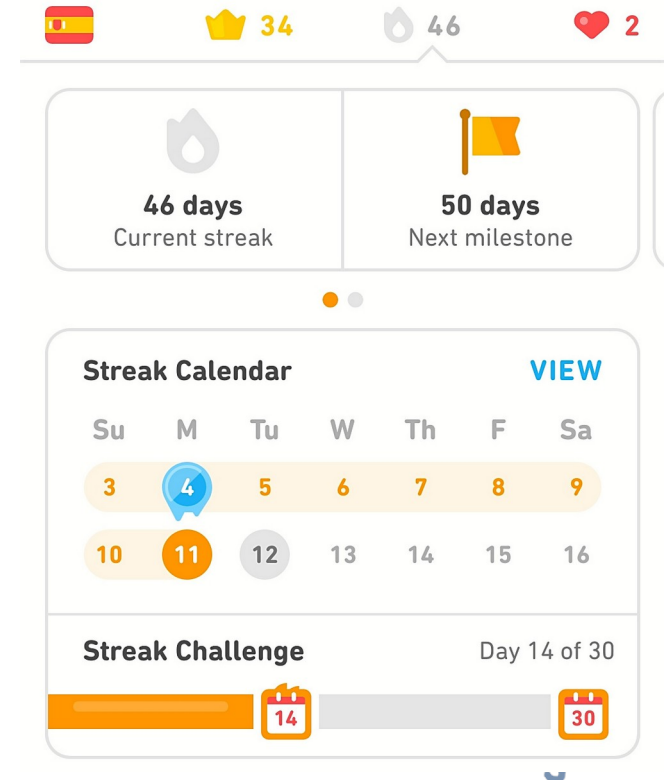


Summit / Camera Progress



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- Recently, LSST project decided to go ahead with “plan B” LSST camera cooling. This means, there will be no more BOT data runs from SLAC (though there is still much interesting to analyse from what we already have)!
- LSST project have indicated more CCD expertise is needed on the summit soon to help with commissioning & tuning auxtel, and comcam during its commissioning
- Thus, DPW is going to be on summit from August 23rd – November 2022 to help out with this effort on site
- Preparations underway (see right + diphtheria vaccine)



Oxford Contribution to CCS/OCS



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OCS – “Observatory Control System”

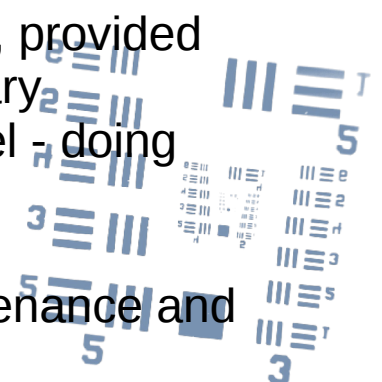
CCS – “Camera Control System”

From Colleague Farrukh Azfar:

-LSST/Rubin camera- team member since 2016, “builder” status, activity: Camera Control System (CCS) & bridge between CCS Observatory Control System (OCS-CCS Bridge)

- 2016-2022: Temps Atomique International, (TAI) time stamping for CCS, provided automated software generation and test, & major portion of bridge, Auxiliary Telescope - now deployed to summit with Commissioning Camera, AuxTel - doing telemetry right now - it works ! (*)

- Current : Extending CCS, OCS-CCS Bridge to actual camera and maintenance and operational support



Thanks



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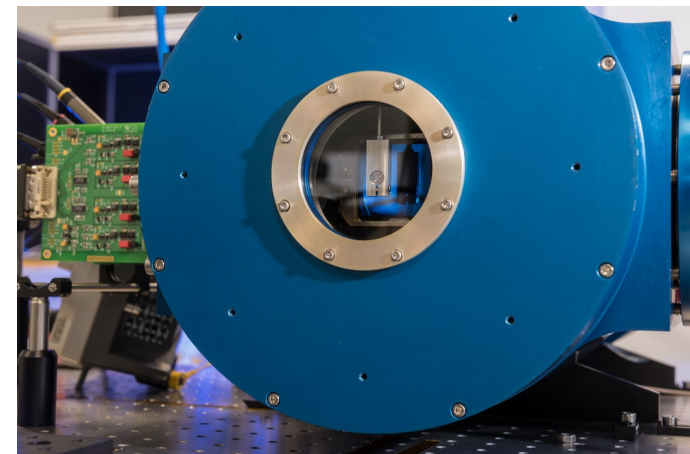
Daniel.weatherill@physics.ox.ac.uk



special thanks to all our 3rd year / summer project students on LSST instrumentation over the years:

- Nicholas Demetriou (Summer 2018)
- Sergio Garcia (Summer 2019)
- Mingyu Liu (2019/20)
- Esther Hung (2019/20)
- Fiona Zhang (2021/22)

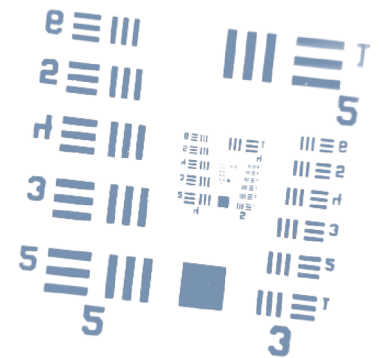
Any questions, comments, discussions you wish to have about LSST instrumentation please do not hesitate to get in touch (before February 2023 ideally!)



BACKUP



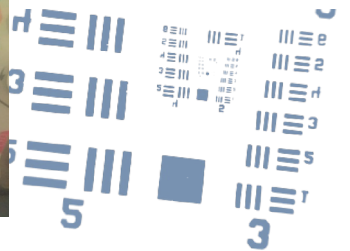
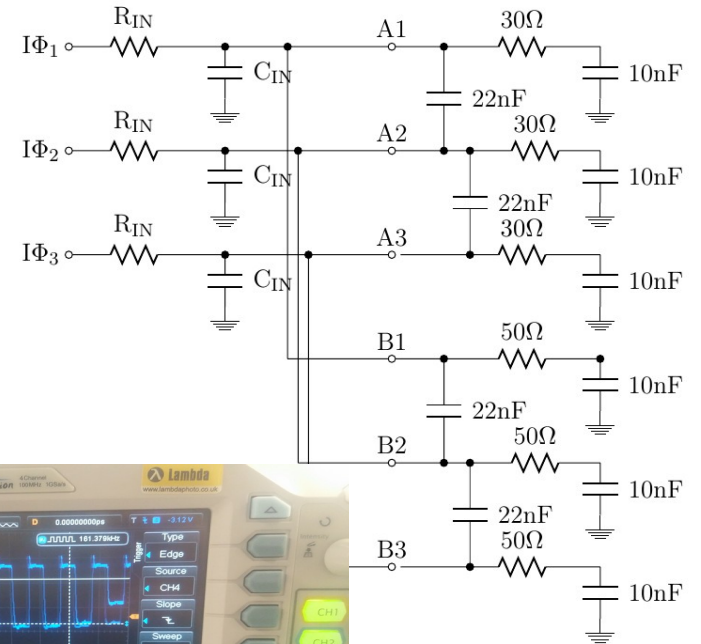
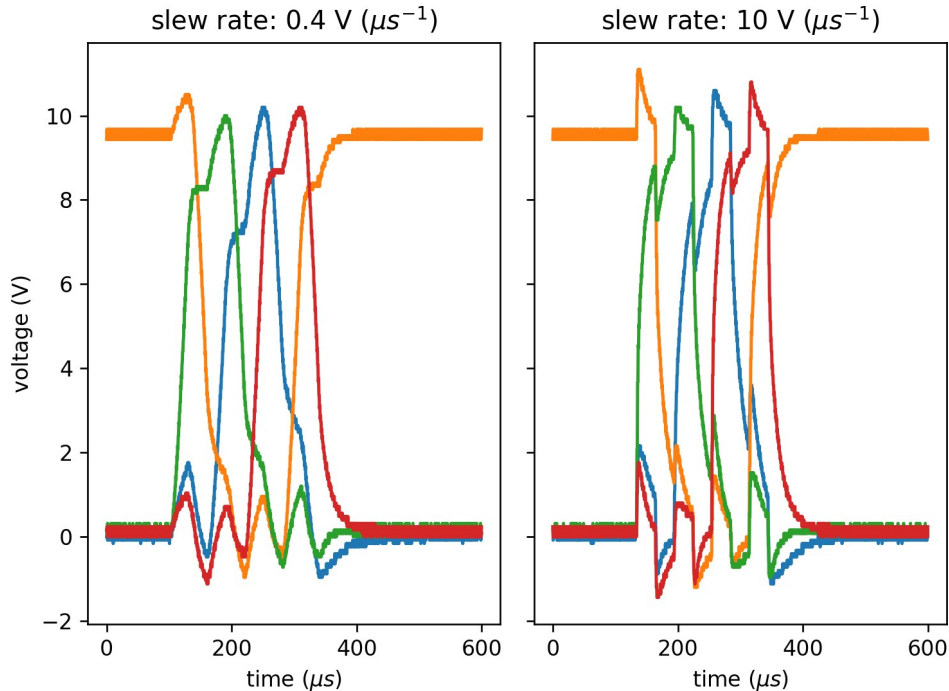
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CCD Clock Optimization



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Astier's Photon Transfer Curve Model



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Image mean

Conventional PTC

Quadratic Fit

Relationship between BFE coefficients

Noise / offsets

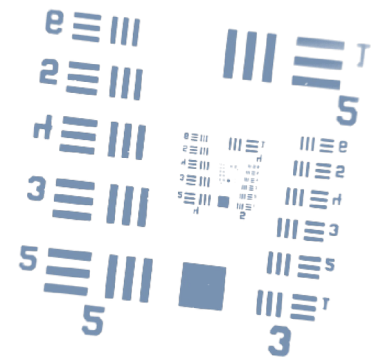
Camera Gain

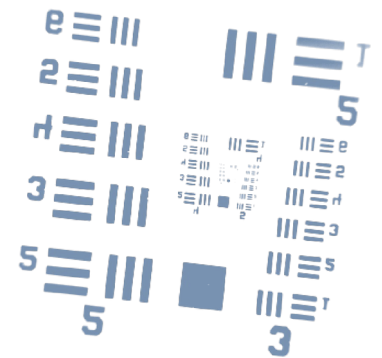
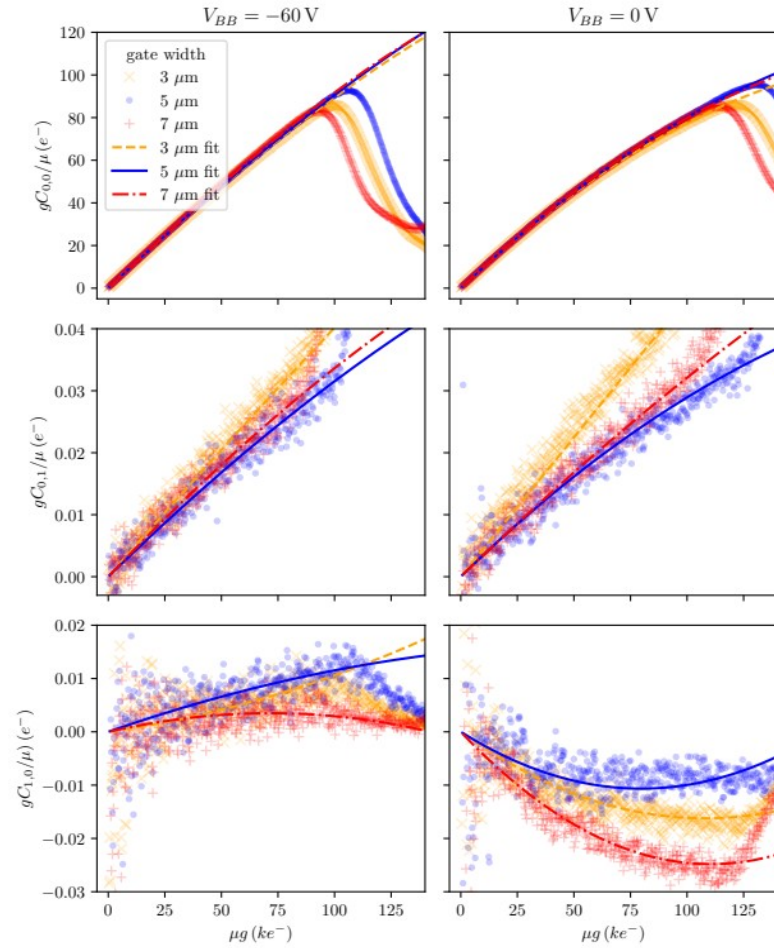
Measured Covariances

Next to leading order BFE relationships

$$C_{ij} = \frac{\mu}{g} \left(\delta_{i0}\delta_{j0} + a_{ij}\mu g + \frac{2}{3} [\mathbf{a} * \mathbf{a} + \mathbf{a} \circ \mathbf{b}]_{ij} (\mu g)^2 + \frac{1}{6} [2\mathbf{a} * \mathbf{a} * \mathbf{a} + 5\mathbf{a} * (\mathbf{a} \circ \mathbf{b})]_{ij} (\mu g)^3 \right) + \frac{n_{ij}}{g^2}$$

Equation from work of Astier et al (2019)

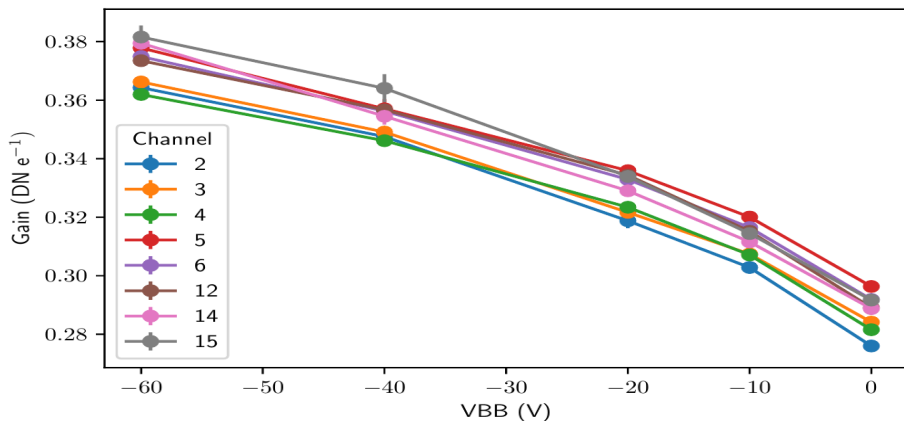




Clock Voltage Optimisation



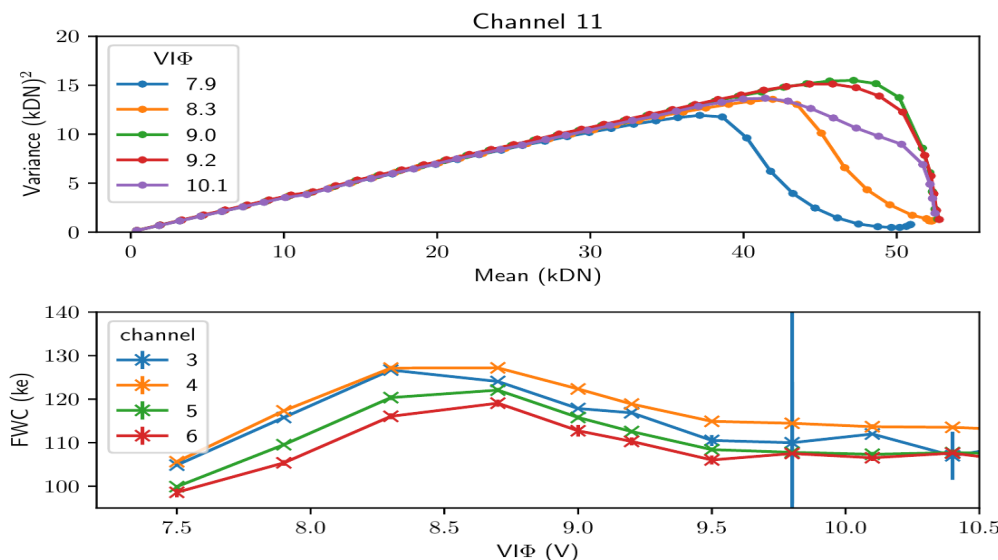
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Back-side biasing means that gain and full well capacity change with applied voltage (unlike a regular CCD!). This is because the sense node capacitance is influenced by the biasing field

In 2017, investigated these relationships with a view to optimising both the back and front side clock voltages.

Discovered it is quite easy to operate the LSST devices in a surface transport regimen. Much has moved on since then, including the introduction of bipolar clocking to combat “tearing” issue

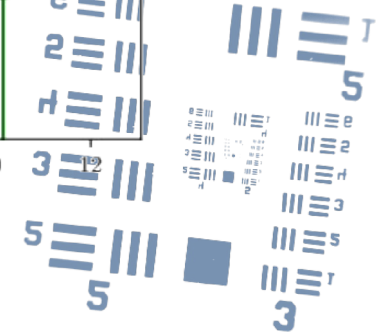
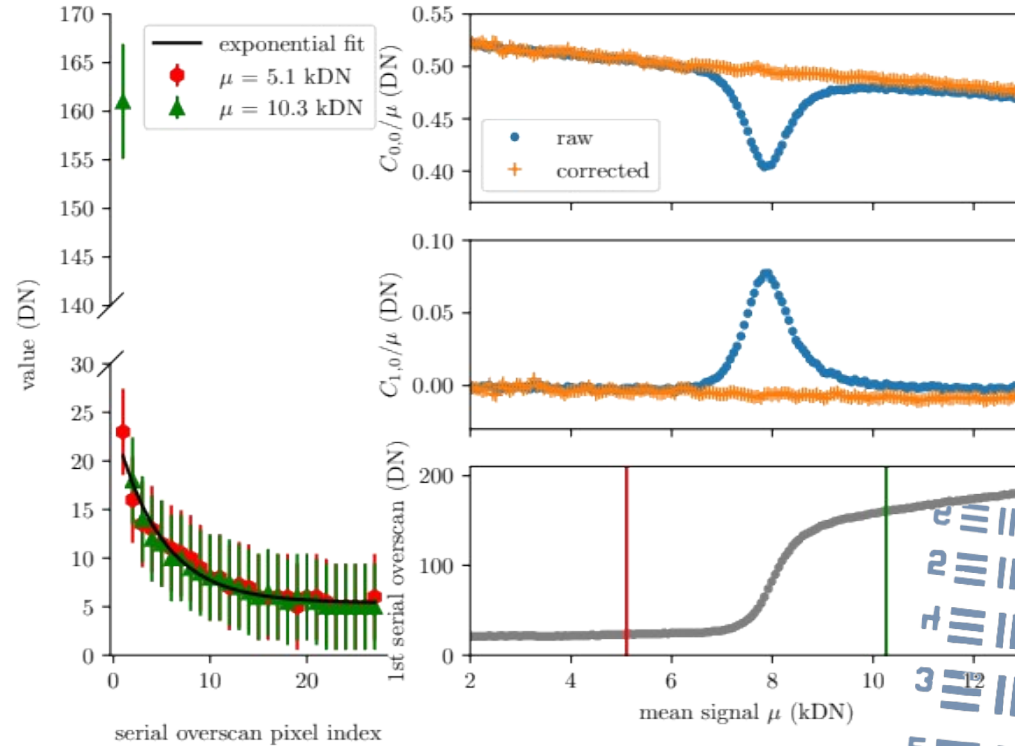


CTI Correction for ISR



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- Signal dependent CTI causes peaks in first serial correlation (and dip in variance)
- Correction using iterated simulated image trailing after fitting EPER measurements (c.f. Massey et al)

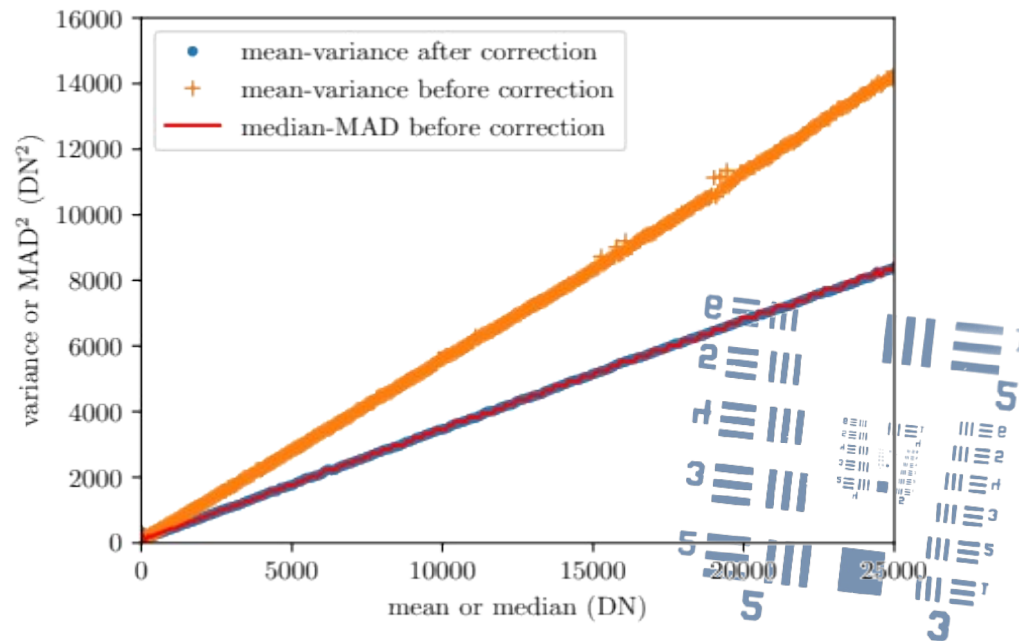


Tearing Correction



- Time varying “tearing” patterns cause excess variance due to incomplete cancellation on subtraction (left)

- We mask these using iterative sigma clipping of the absolute value of the difference image
- After correction, mean variance curve lines up well with median-MAD curve, not affected by outliers (right)



Trap Pumping Theory



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Integer prefactors can change depending on the clocking scheme used to pump

$$I = N_{\text{pump}} P_c \left(\exp\left(\frac{-2t_{\text{ph}}}{\tau_e}\right) - \exp\left(\frac{3t_{\text{ph}}}{\tau_e}\right) \right)$$

Final measured signal includes prefactor for Number of pumps and probability of capture (we assume instant capture)

Theoretical emission time comes from Shockley – Reed- Hall theory. Depends on:

- Trap cross section (reciprocally)
- Temperature (exponentially + polynomially)
- Local electron density (reciprocally)

Electron density

$$\tau_c = \frac{1}{\sigma n v_{th}}$$

$$\tau_e = \frac{1}{X \chi \sigma N_c v_{th}} \exp\left(\frac{E}{kT}\right)$$

$$N_c = 2 \left(\frac{2\pi m_{dos} kT}{h^2} \right)^{\frac{3}{2}}$$

$$v_{th} = \sqrt{\frac{3kT}{m_c}}$$

$$P_x = 1 - \exp\left(\frac{-t}{\tau_x}\right)$$



Single trap-pumping



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Temperature range -30°C to -100°C , in 5°C intervals.

Capture 5 bias and 5 flat-field images per temperature.

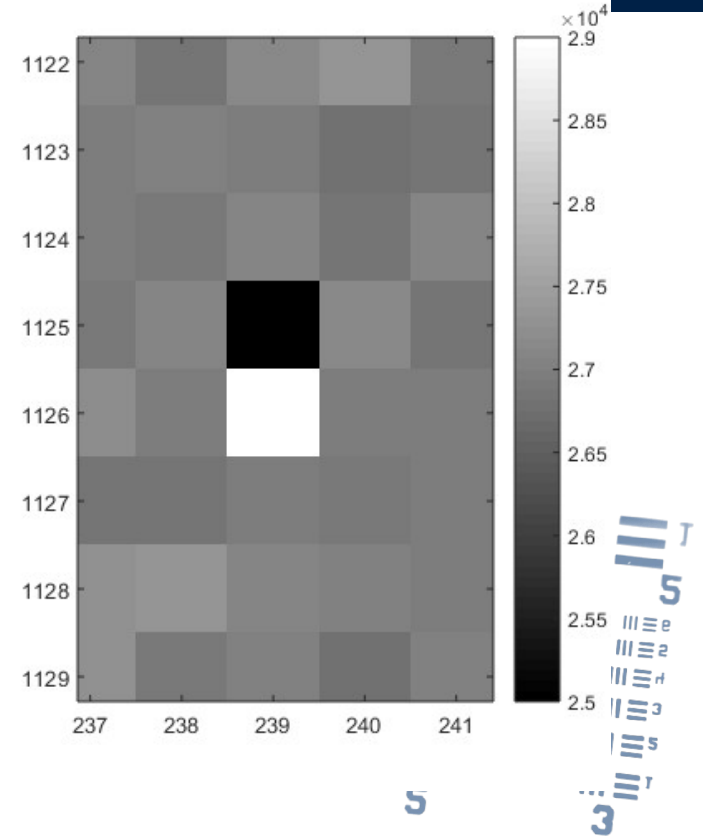
Capture 5 trap-pumped images with N=50000 at each phasetime, from 10μs to 1000μs.

Average and background subtract, then locate dipoles through thresholding on signal level.

Plot dipole intensity simply as $\frac{1}{2} * (\text{bright pixel signal} - \text{dark pixel signal})$ across entire phasetime range.

Fit intensity curves based on SRH to determine capture and emission time constants.

$$\frac{I}{N} = A \left(\left(1 - e^{-\frac{t}{\tau_c}} \right) \left(e^{-\frac{2t}{\tau_e}} - e^{-\frac{3t}{\tau_e}} \right) \right) + d$$

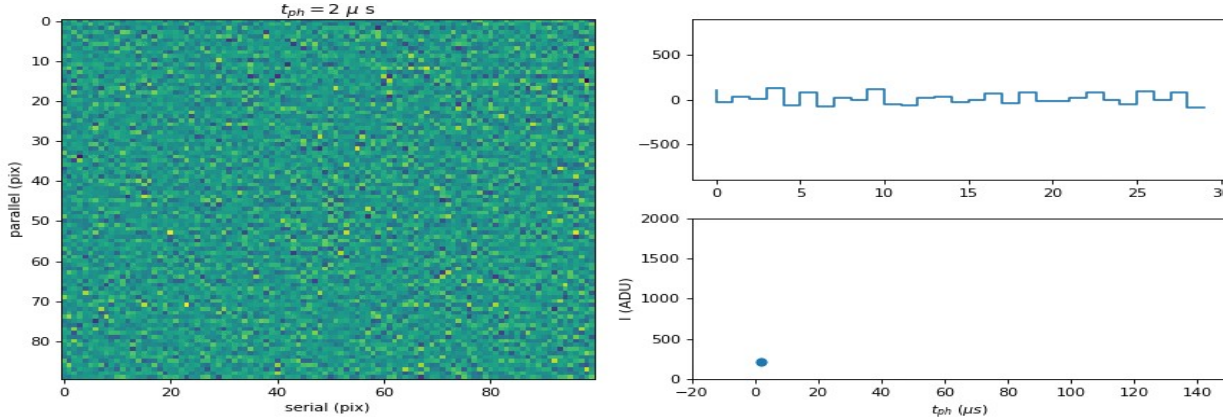


Trap Pumping In Practice



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If animation not working try here – <http://users.ox.ac.uk/~phys1463//trappump.gif>



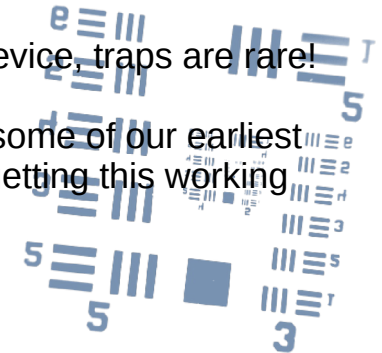
Procedure: expose to light, then pump a large number of times, varying dwell time. We also take unpumped flats for reference.

Find traps by simple sigma thresholding (with a goodness of fit cut after fitting emission time curve).

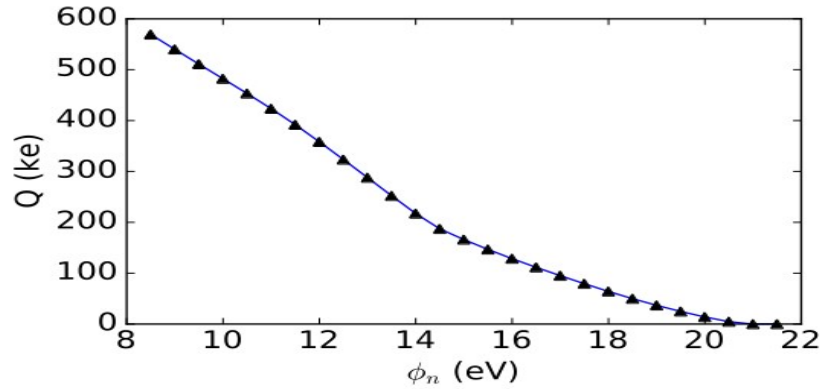
We typically can get away with 4 sigma exclusion.

In an unirradiated device, traps are rare!

Animation on left – some of our earliest (2018) attempts at getting this working on the CCD250

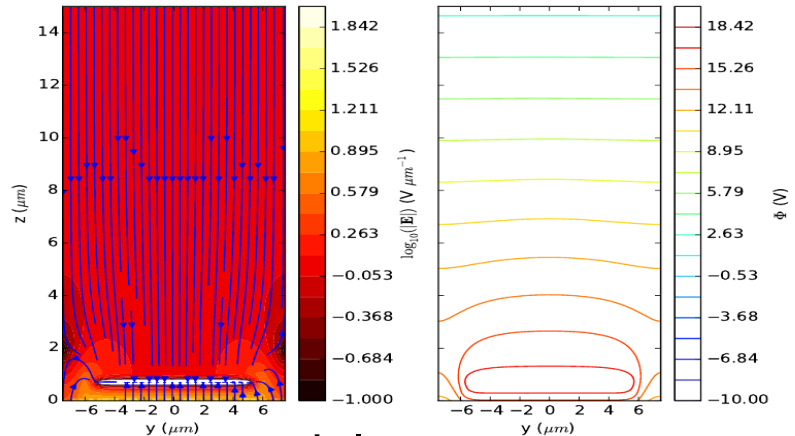


Charge Storage: TCAD modelling

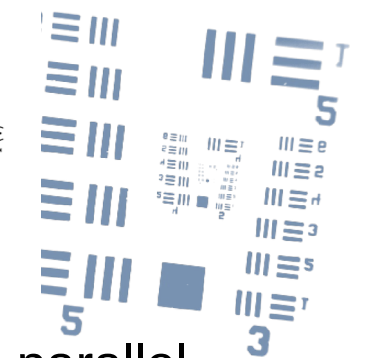
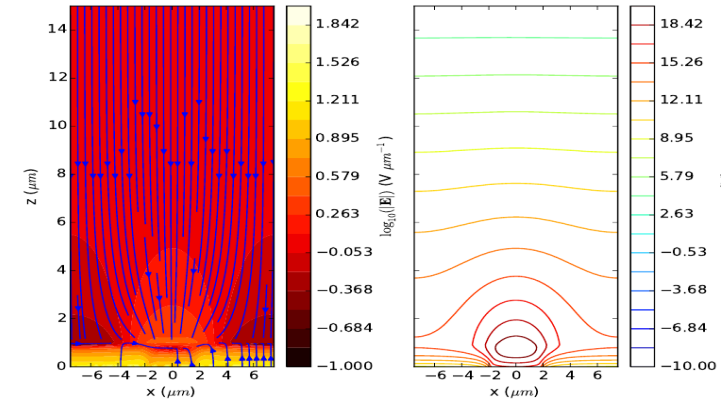


Procedure for modelling charge storage in TCAD:

- 1) solve equilibrium PE
- 2) solve applied bias PE
- 3) force (“Hand of God”) a small change in electron QFL
- 4) solve continuity & do small transient timestep
- 5) solve steady state continuity & PE
- 6) repeat 3-5 until desired electron QFL is reached

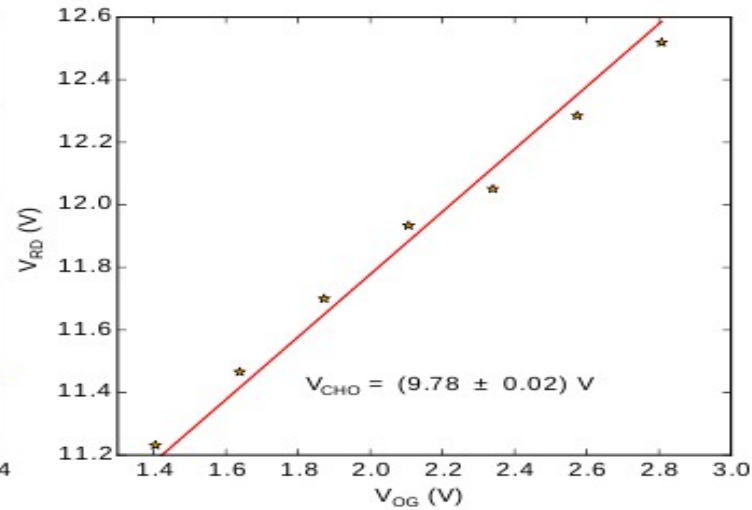
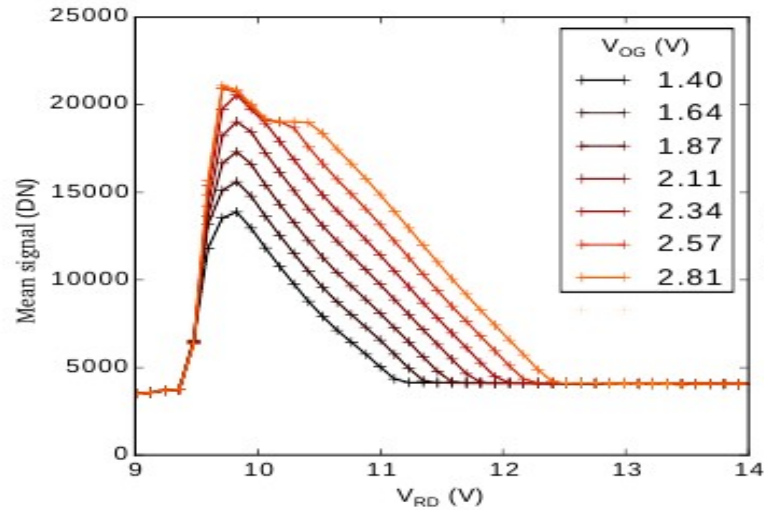


serial



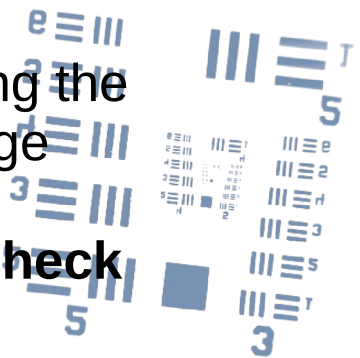
parallel

Estimating parameters for TCAD simulation



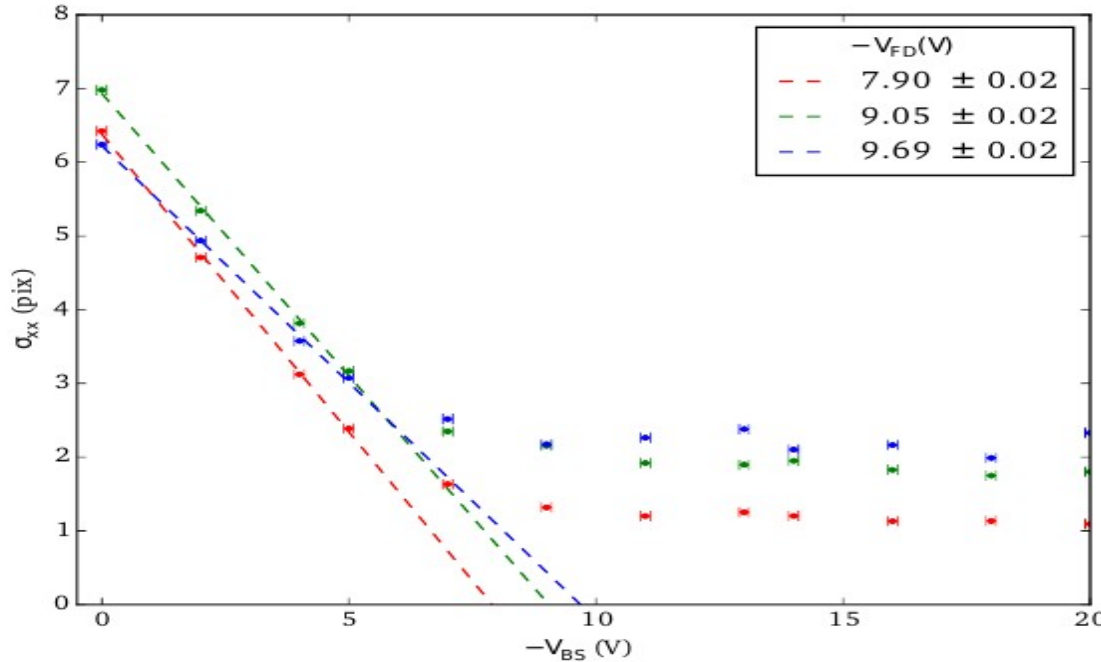
1) measure the channel parameter using a standard method of finding the reset drain and output gate potentials which cause the onset of charge injection from the reset transistor to the output node.

All TCAD simulations sanity checked against this number (i.e. check that empty channel gives correct potential extremum)



Estimating parameters for TCAD simulation

Estimate substrate acceptor density using the full-depletion voltage:

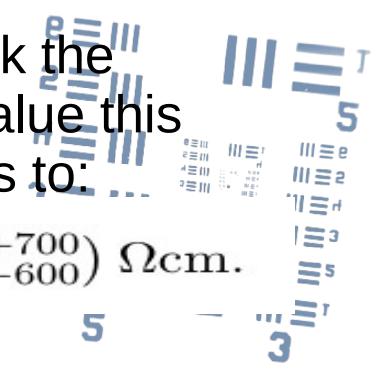


$$V_{BS} = V_{\max} + \frac{q_e N_A}{2\epsilon_{\text{si}}\epsilon_0} (z_T - \sigma_{xx})^2.$$

$$N_A = (2.0 \pm 0.2) \times 10^{12} \text{ cm}^{-3}$$

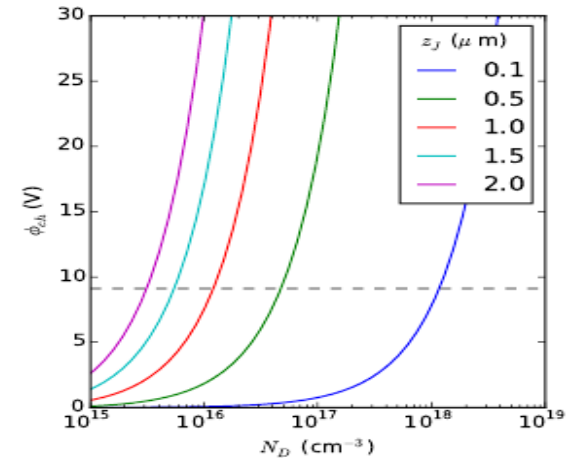
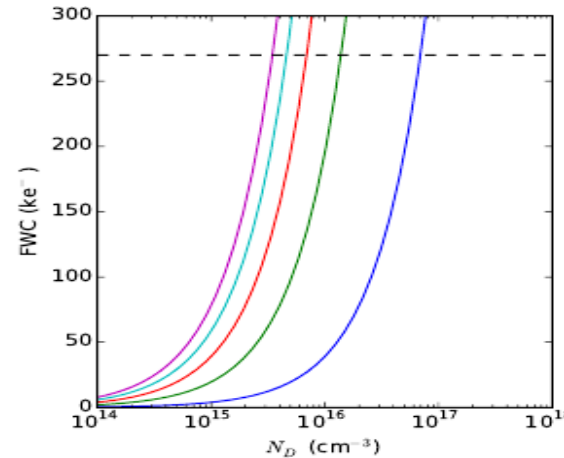
- Sanity check the resistivity value this corresponds to:

$$\rho = (6600_{-600}^{+700}) \Omega\text{cm}.$$



Estimating parameters for TCAD simulation

- Use the (approximate) 1D analytic solutions to Poisson's equation to construct constraints on donor density and junction depth against measurements of (maximum) full-well and channel potential



$$z'_j = z_J - \frac{Q}{2N_D y_B L}$$

$$z_0 = z'_J - \sqrt{\frac{2\epsilon_{si}\epsilon_0 N_A V_m}{q_e N_D (N_A + N_D)}}$$

$$z_1 = z_J - \sqrt{\frac{2\epsilon_{si}\epsilon_0 N_A V_m}{q_e N_D (N_A + N_D)}}$$

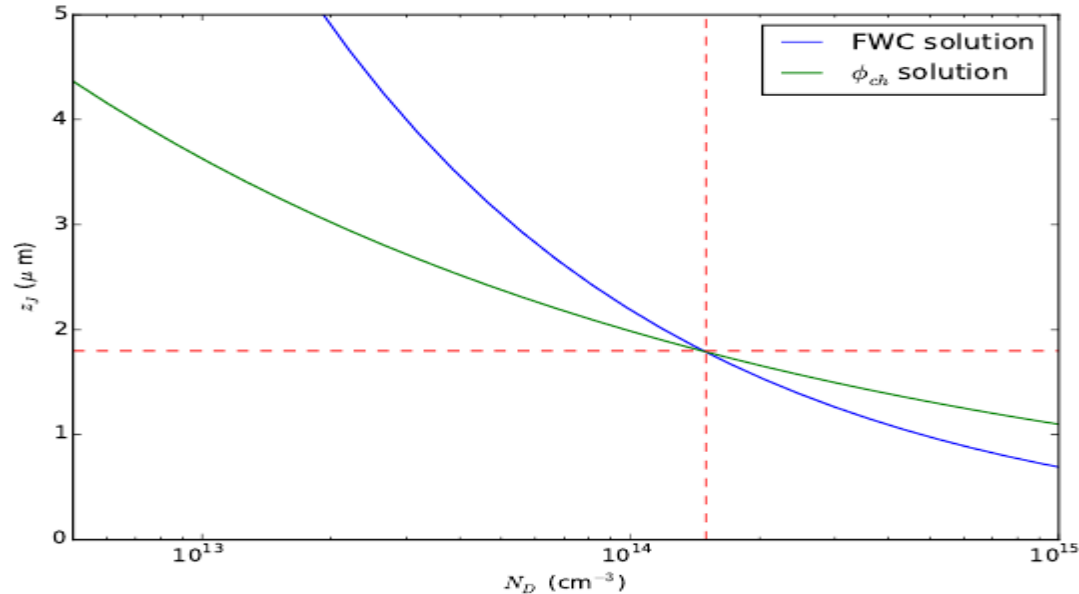
$$V_m = \left(1 + \frac{N_A}{N_D}\right) \left(V_G + V_1 + V_2 - \sqrt{V_2^2 + 2V_2(V_1 + V_G)}\right)$$

with $V_1 = \frac{q_e N_D (z'_J)^2}{2\epsilon_{si}\epsilon_0} \left(1 + \frac{2\epsilon_{si}d_{ox}}{\epsilon_{ox}z_t}\right)$

$$V_2 = \frac{q_e N_A (z'_J)^2}{\epsilon_{si}\epsilon_0} \left(1 + \frac{\epsilon_{si}d_{ox}}{\epsilon_{ox}z_t}\right)^2$$

$e \equiv III \dots$

Estimating parameters for TCAD simulation



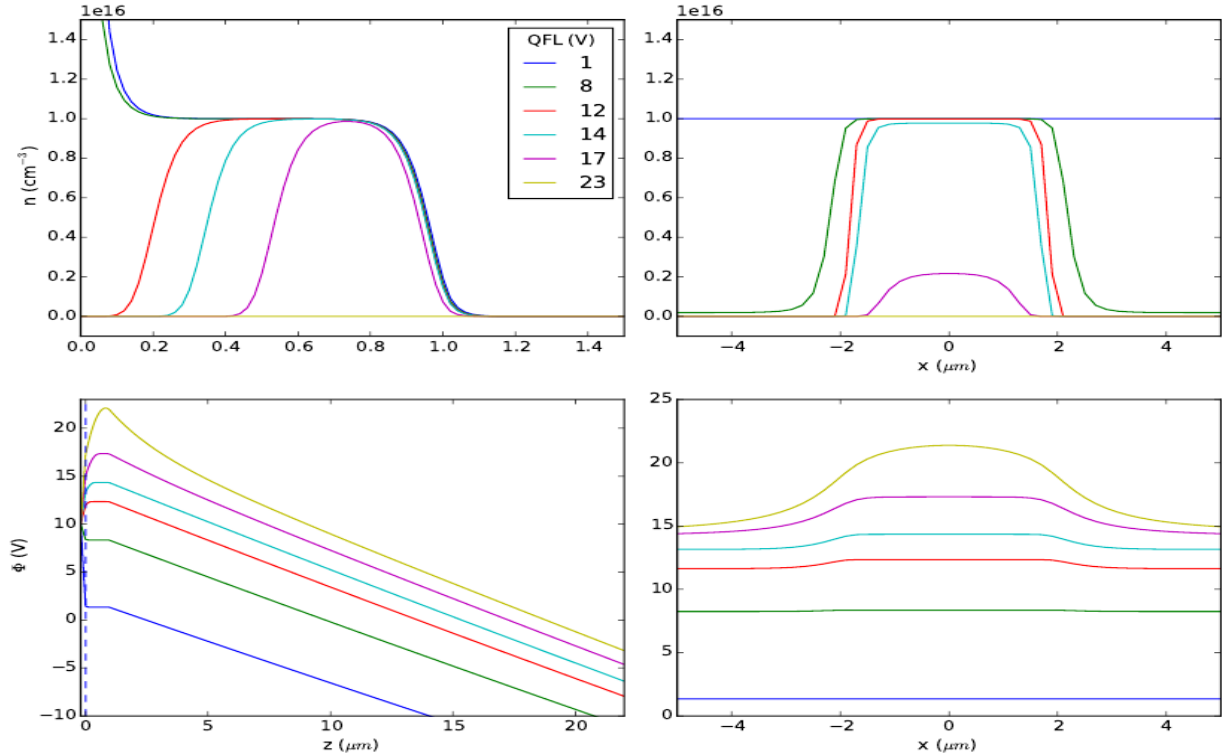
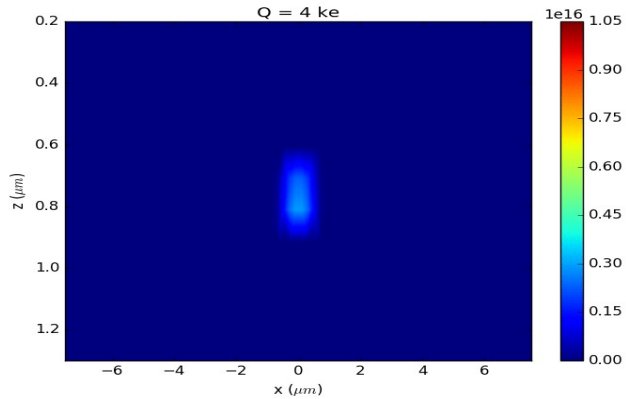
- The numerical parameters needed for the simulation (oxide thickness, device thickness, donor density, acceptor density, junction depth) then all have estimates consistent with measurements
- Use these parameters as starting point and make sure channel potential is consistent



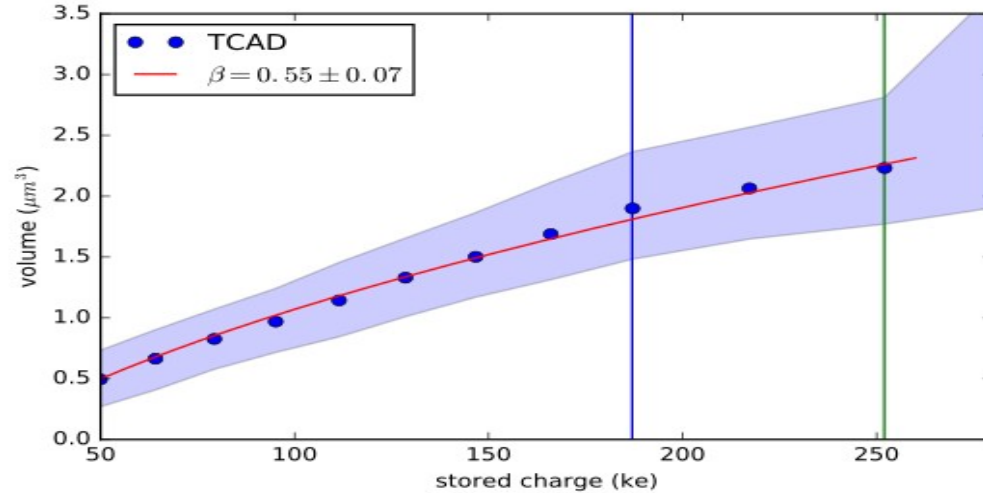
Charge Storage: TCAD modelling

Changing QFL this way allows modelling of reset pixels without the inclusion of a drain contact in the pixel

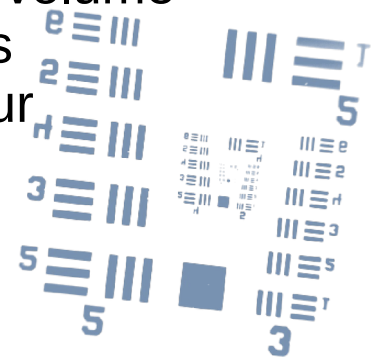
Blooming and surface contact effects both clear – junction depth = 1 μm , Oxide interface @ $z=0.2 \mu\text{m}$



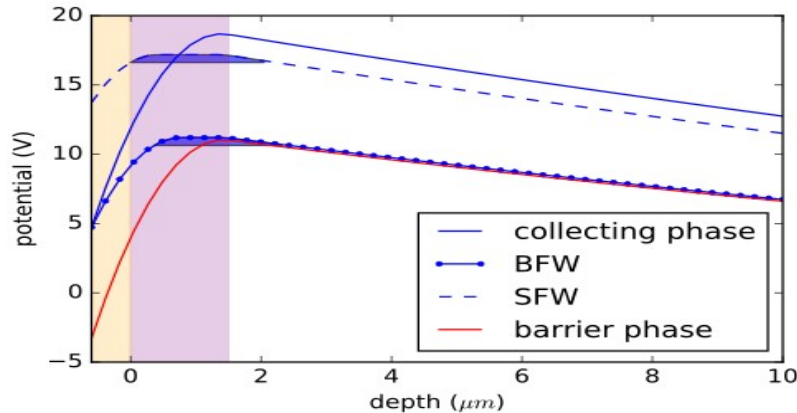
TCAD Charge-Volume calculation



- By drawing contours around electron concentration solutions, volume can be estimated without resorting to rectangular assumptions
- Shaded area represents bound of taking 99.9% charge contour (upper bound) to 90% charge contour (lower bound)
- Note reasonably good power law fit to $\beta = (0.55 \pm 0.07)$
-



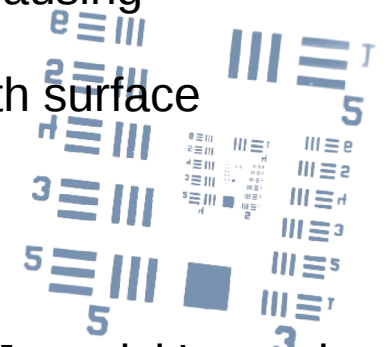
Full Well Capacity - Background



- Important to have full-well characteristics matched by charge storage model (because they are linked via the density)
- Full well transfer usually used to optimize collecting phase potential

- Bloomed Full Well (BFW) → clock level becomes low enough that the collecting phase potential overlaps the barrier phase potential causing blooming
- Surface Full Well (SFW) → charge packet begins to interact with surface traps before charge can spill into barrier phase

“Optimum”* Full Well when Image clocks set such that
 $BFW \approx SFW$

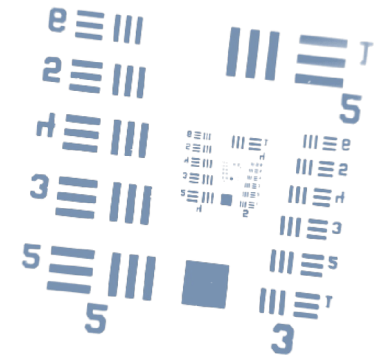
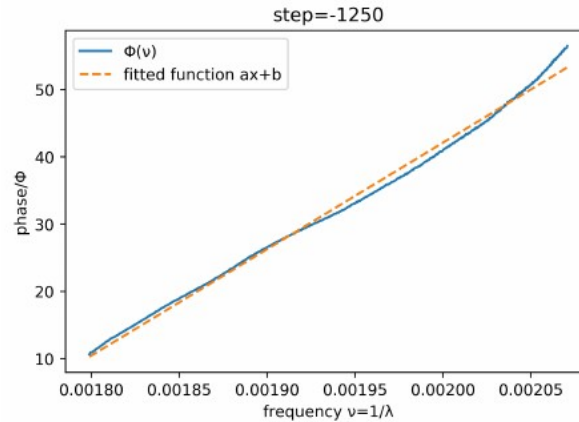
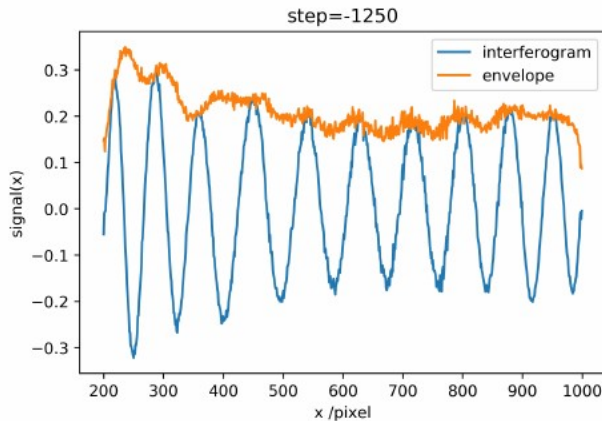
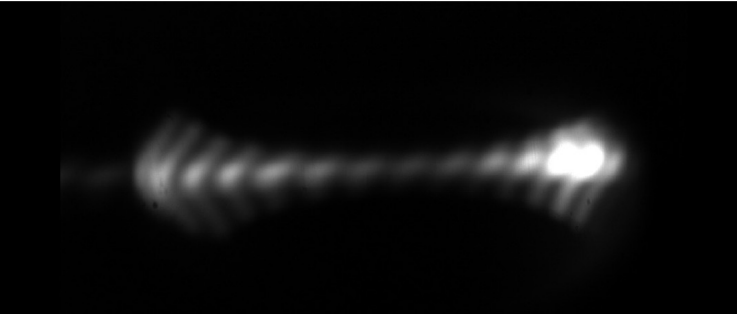


*Jim Janesick's word

Steps so far

We carefully calibrated the interferometer using two arms with mirrors (to be replaced with cameras later).

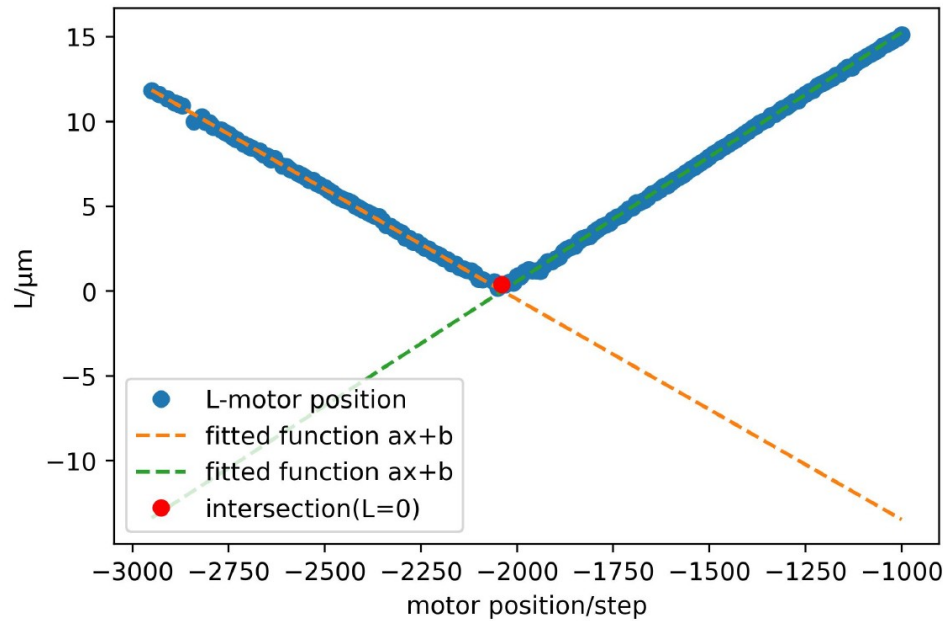
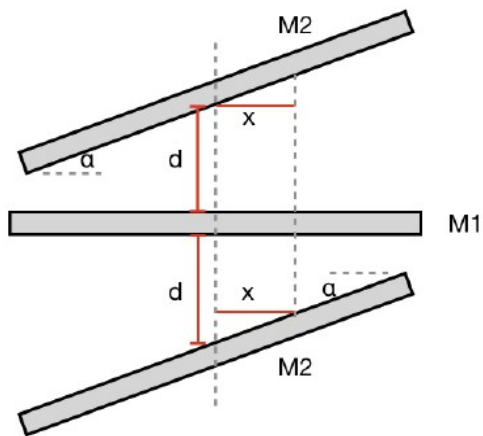
We produce interferograms on white light (left) from which we can extract a phase function (below) and from that, a distance measurement (more details in previous update talk!)



Scanning Mirror Position



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With the mirror surfaces, we've been able to align the two arms to a (compensated) differential length now $< 2\mu\text{m}$ at centre.

We think there is still a tilt error, as evidenced by the differing slopes either Side of 0, and more evidence later

